

Product Description

The PE4245 RF Switch is designed to cover a broad range of applications from near DC to 4000 MHz. This switch integrates on-board CMOS control logic with a low voltage CMOS compatible control input. Using a +3-volt nominal power supply voltage, a 1 dB compression point of +27 dBm can be achieved. The PE4245 also exhibits excellent isolation of better than 42 dB at 1000 MHz and is offered in a small 3x3 mm DFN package.

The PE4245 is manufactured on Peregrine's UltraCMOS™ process, a patented variation of silicon-on-insulator (SOI) technology on a sapphire substrate, offering the performance of GaAs with the economy and integration of conventional CMOS.

Figure 1. Functional Diagram

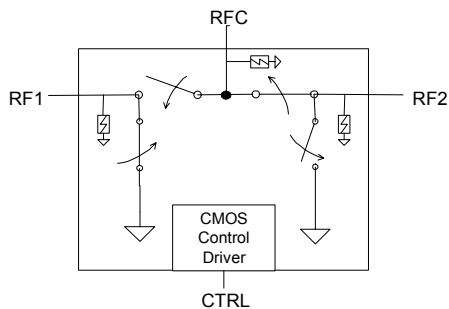


Figure 2. Package Type

6-lead DFN



Table 1. Electrical Specifications @ +25 °C, V_{DD} = 3 V (Z_S = Z_L = 50 Ω)

Parameter	Conditions	Minimum	Typical	Maximum	Units
Operation Frequency ¹		DC		4000	MHz
Insertion Loss	1000 MHz 2000 MHz		0.6 0.7	0.75 0.85	dB dB
Isolation – RFC to RF1/RF2	1000 MHz 2000 MHz	39 30	42 32		dB dB
Isolation – RF1 to RF2	1000 MHz 2000 MHz	34 27	36 29		dB dB
Return Loss	1000 MHz 2000 MHz	21 20	23 22		dB dB
'ON' Switching Time	CTRL to 0.1 dB final value, 2 GHz		200		ns
'OFF' Switching Time	CTRL to 25 dB isolation, 2 GHz		90		ns
Video Feedthrough ²			15		mV _{pp}
Input 1 dB Compression	2000 MHz	26	27		dBm
Input IP3	2000 MHz, 14 dBm	43	45		dBm

Notes: 1. Device linearity will begin to degrade below 10 MHz.

2. The DC transient at the output of any port of the switch when the control voltage is switched from Low to High or High to Low in a 50 Ω test set-up, measured with 1ns risetime pulses and 500 MHz bandwidth.

Figure 3. Pin Configuration

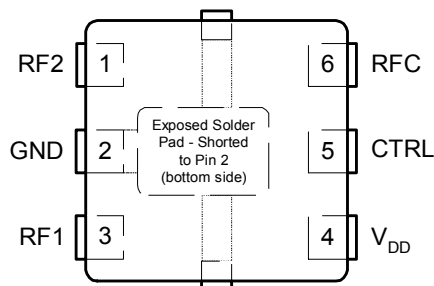


Table 2. Pin Descriptions

Pin No.	Pin Name	Description
1	RF2	RF2 port (Note 1)
2	GND	Ground Connection. Traces should be physically short and connected to the ground plane. This pin is connected to the exposed solder pad that also must be soldered to the ground plane for best performance.
3	RF1	RF1 port (Note 1)
4	V _{DD}	Nominal 3 V supply connection.
5	CTRL	CMOS logic level: High = RFC to RF1 signal path Low = RFC to RF2 signal path
6	RFC	Common RF port for switch (Note 1)

Notes: 1. All RF pins must be DC blocked with an external series capacitor or held at 0 V_{DC}.

Table 3. DC Electrical Specifications

Parameter	Min	Typ	Max	Units
V _{DD} Power Supply Voltage	2.7	3.0	3.3	V
I _{DD} Power Supply Current V _{DD} = 3V, V _{CTRL} = 3V		250	500	nA
Control Voltage High	0.7x V _{DD}			V
Control Voltage Low			0.3x V _{DD}	V

Table 4. Absolute Maximum Ratings

Symbol	Parameter/Conditions	Min	Max	Units
V _{DD}	Power supply voltage	-0.3	4.0	V
V _I	Voltage on any input	-0.3	V _{DD} + 0.3	V
T _{ST}	Storage temperature range	-65	150	°C
T _{OP}	Operating temperature range	-40	85	°C
P _{IN}	Input power (50Ω)		30	dBm
V _{ESD}	ESD voltage (Human Body Model)		1500	V

Absolute Maximum Ratings are those values listed in the above table. Exceeding these values may cause permanent device damage. Functional operation should be restricted to the limits in the DC Electrical Specifications table. Exposure to absolute maximum ratings for extended periods may affect device reliability.

Table 5. Control Logic Truth Table

Control Voltage	Signal Path
CTRL = CMOS High	RFC to RF1
CTRL = CMOS Low	RFC to RF2

Electrostatic Discharge (ESD) Precautions

When handling this UltraCMOS™ device, observe the same precautions that you would use with other ESD-sensitive devices. Although this device contains circuitry to protect it from damage due to ESD, precautions should be taken to avoid exceeding the rating specified in Table 4.

Latch-Up Avoidance

Unlike conventional CMOS devices, UltraCMOS™ devices are immune to latch-up.

Typical Performance Data @ 25 °C (Unless Otherwise Noted)

Figure 4. Insertion Loss - RFC to RF1
T = -40 °C to 85 °C

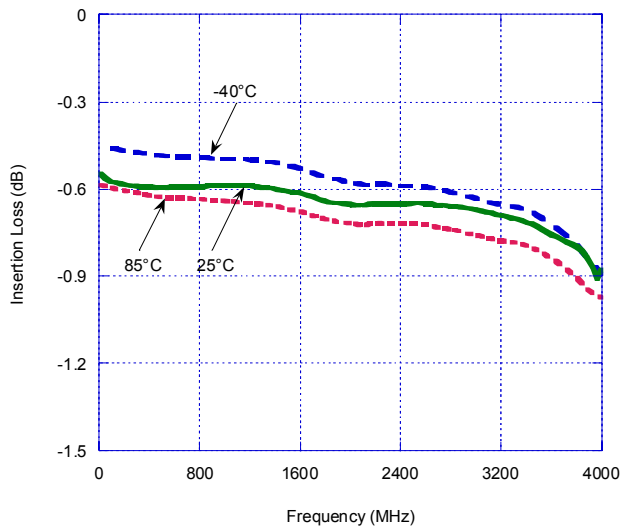


Figure 5. Input 1dB Compression Point and IIP3

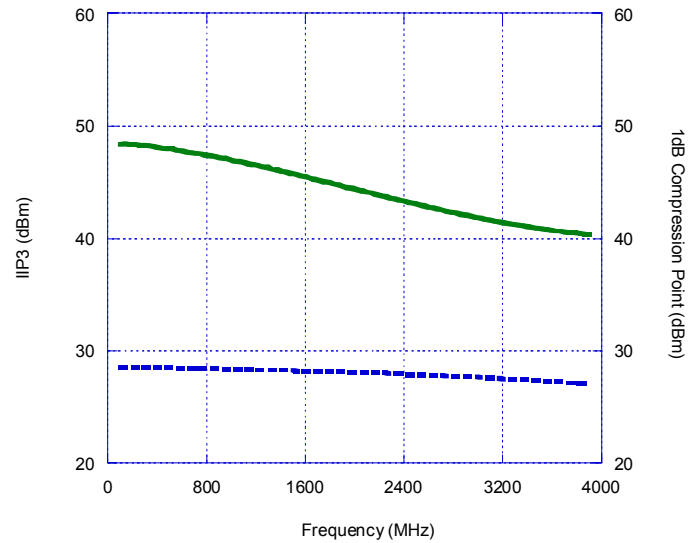


Figure 6. Insertion Loss - RFC to RF2
T = -40 °C to 85 °C

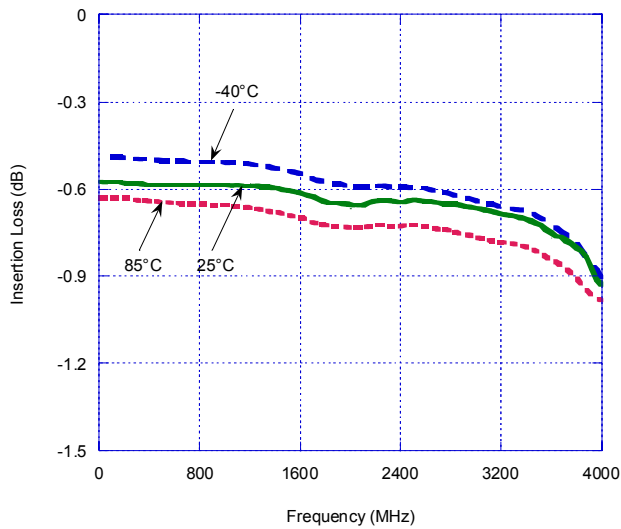
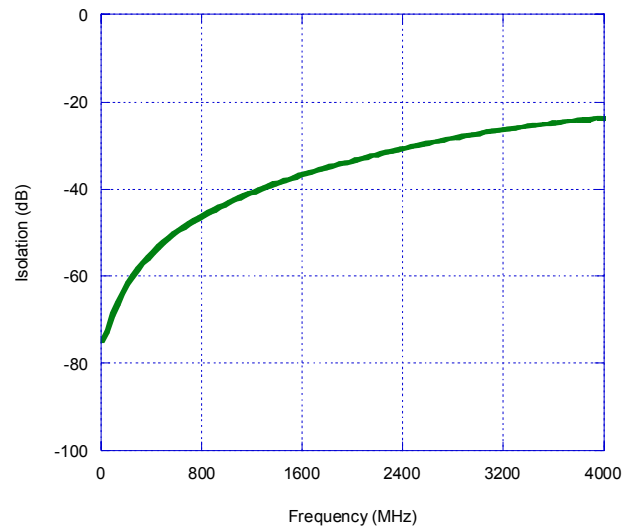


Figure 7. Isolation - RFC to RF1



Typical Performance Data @ 25 °C

Figure 8. Isolation – RFC to RF2

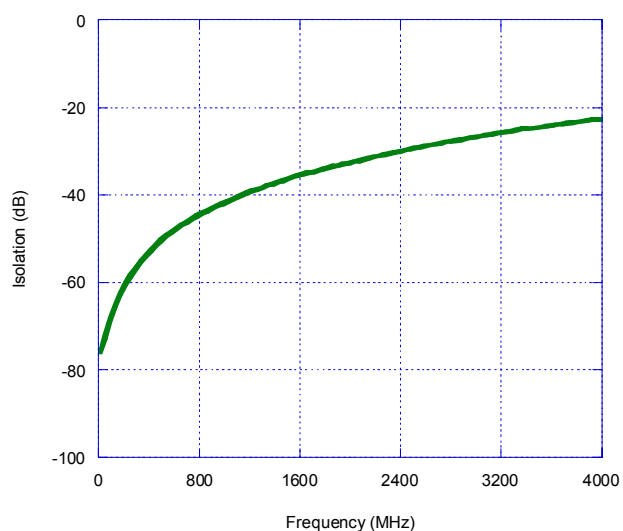


Figure 9. Isolation – RF1 to RF2, RF2 to RF1

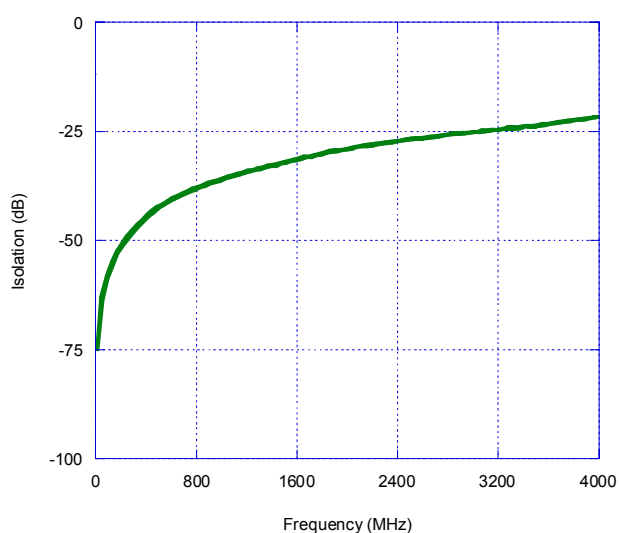


Figure 10. Return Loss – RFC to RF1, RF2

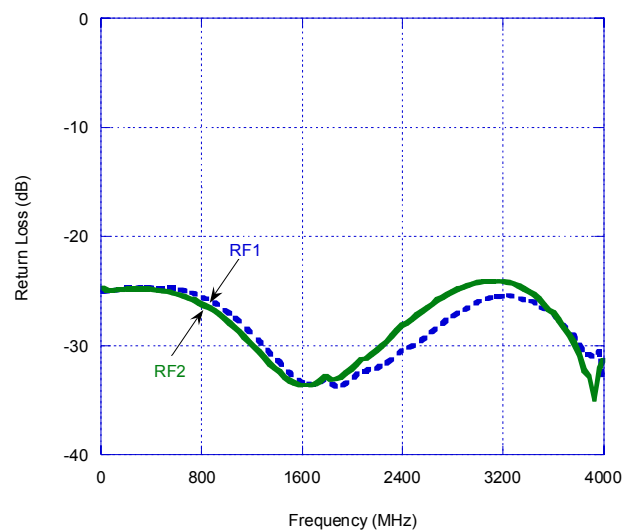
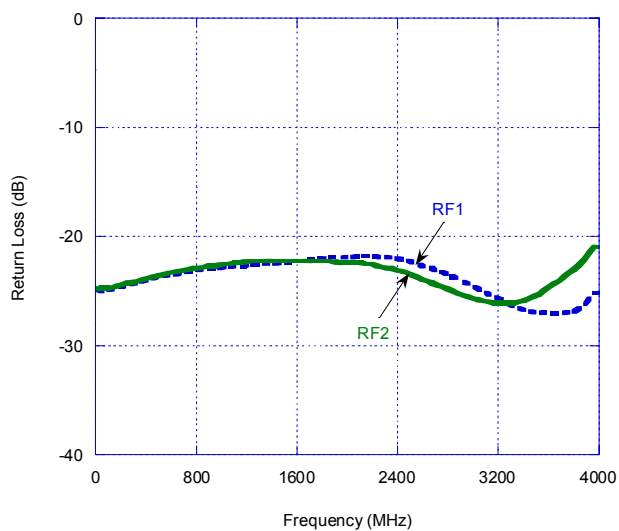


Figure 11. Return Loss – RF1, RF2



Evaluation Kit

The SPDT Switch Evaluation Kit board was designed to ease customer evaluation of the PE4245 SPDT switch. The RF common port is connected through a 50 Ω transmission line to the top left SMA connector, J1. Port 1 and Port 2 are connected through 50 Ω transmission lines to the top two SMA connectors on the right side of the board, J2 and J3. A through transmission line connects SMA connectors J4 and J5. This transmission line can be used to estimate the loss of the PCB over the environmental conditions being evaluated.

The board is constructed of a two metal layer FR4 material with a total thickness of 0.031". The bottom layer provides ground for the RF transmission lines. The transmission lines were designed using a coplanar waveguide with ground plane model using a trace width of 0.0476", trace gaps of 0.030", dielectric thickness of 0.028", metal thickness of 0.0021" and ϵ_r of 4.4.

J6 provides a means for controlling DC and digital inputs to the device. Starting from the lower left pin, the second pin to the right (J6-3) is connected to the device CNTL input. The fourth pin to the right (J6-7) is connected to the device V_{DD} input.

Figure 12. Evaluation Board Layouts

Peregrine Specification 101/0085

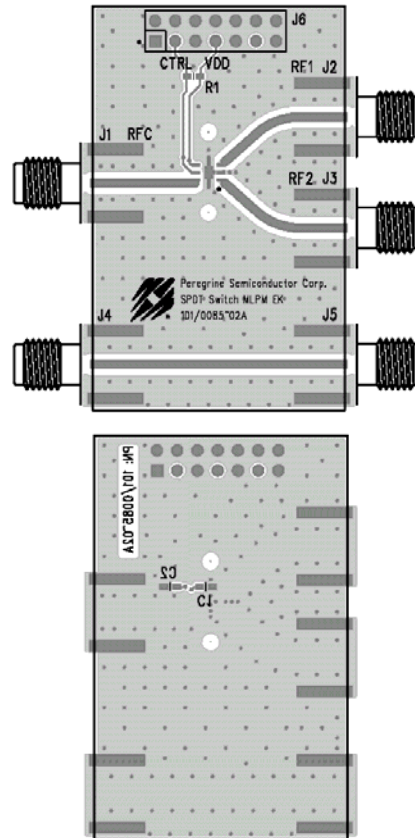
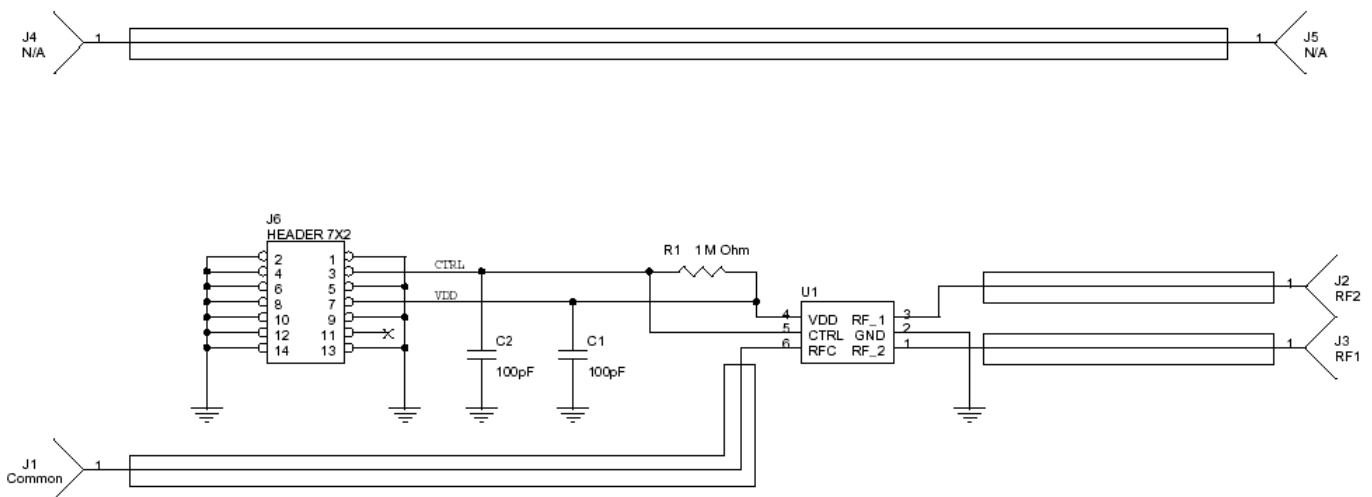
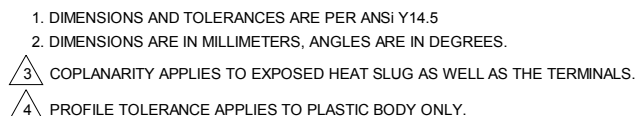


Figure 13. Evaluation Board Schematic

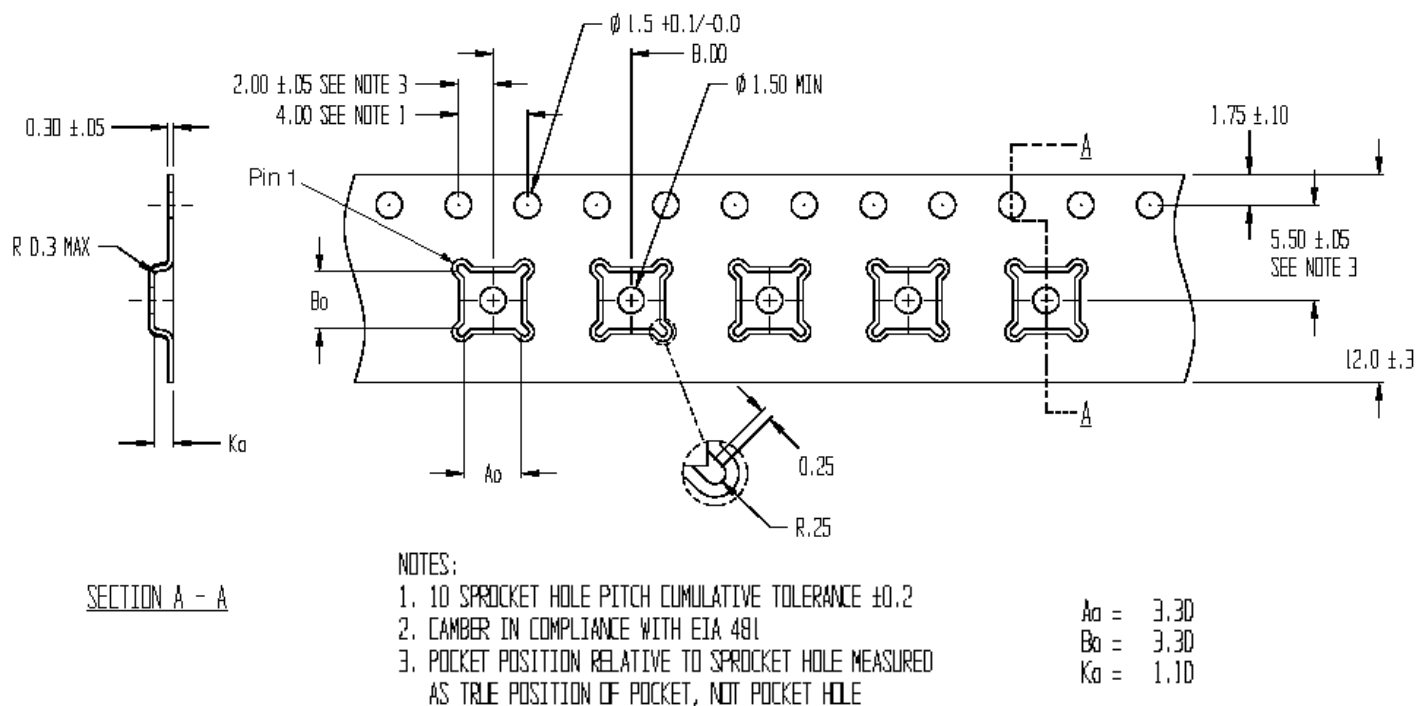
Peregrine Specification 102/0110



6-lead DFN



6-lead DFN



Dimension	DFN 3x3 mm
Ao	3.23 ± 0.1
Bo	3.17 ± 0.1
Ko	1.37 ± 0.1
P	4 ± 0.1
W	8 +0.3, -0.1
T	0.254 ± 0.02
R7 Quantity	3000
R13 Quantity	N.A.

Order Code	Part Marking	Description	Package	Shipping Method
4245-01	4245	PE4245-06DFN 3x3mm-12800F	6-lead 3x3 mm DFN	12800 units / Canister
4245-02	4245	PE4245-06DFN 3x3mm-3000C	6-lead 3x3 mm DFN	3000 units / T&R
4245-00	PE4245-EK	PE4245-06DFN 3x3mm-EK	Evaluation Kit	1 / Box
4245-51	4245	PE4245G-06DFN 3x3mm-12800F	Green 6-lead 3x3 mm DFN	12800 units / Canister
4245-52	4245	PE4245G-06DFN 3x3mm-3000C	Green 6-lead 3x3 mm DFN	3000 units / T&R

Sales Offices

The Americas

Peregrine Semiconductor Corporation

9450 Carroll Park Drive
San Diego, CA 92121
Tel: 858-731-9400
Fax: 858-731-9499

Europe

Peregrine Semiconductor Europe

Bâtiment Maine
13-15 rue des Quatre Vents
F-92380 Garches, France
Tel: +33-1-47-41-91-73
Fax : +33-1-47-41-91-73

Space and Defense Products

Americas:

Tel: 858-731-9453

Europe, Asia Pacific:

180 Rue Jean de Guirmand
13852 Aix-En-Provence Cedex 3, France
Tel: +33(0) 4 4239 3361
Fax: +33(0) 4 4239 7227

North Asia Pacific

Peregrine Semiconductor K.K.

Teikoku Hotel Tower 10B-6
1-1-1 Uchisaiwai-cho, Chiyoda-ku
Tokyo 100-0011 Japan
Tel: +81-3-3502-5211
Fax: +81-3-3502-5213

Peregrine Semiconductor, Korea

#B-2402, Kolon Tripolis, #210
Geumgok-dong, Bundang-gu, Seongnam-si
Gyeonggi-do, 463-480 S. Korea
Tel: +82-31-728-4300
Fax: +82-31-728-4305

South Asia Pacific

Peregrine Semiconductor, China

Shanghai, 200040, P.R. China
Tel: +86-21-5836-8276
Fax: +86-21-5836-7652

For a list of representatives in your area, please refer to our Web site at: www.psemi.com

Data Sheet Identification

Advance Information

The product is in a formative or design stage. The data sheet contains design target specifications for product development. Specifications and features may change in any manner without notice.

Preliminary Specification

The data sheet contains preliminary data. Additional data may be added at a later date. Peregrine reserves the right to change specifications at any time without notice in order to supply the best possible product.

Product Specification

The data sheet contains final data. In the event Peregrine decides to change the specifications, Peregrine will notify customers of the intended changes by issuing a DCN (Document Change Notice).

The information in this data sheet is believed to be reliable. However, Peregrine assumes no liability for the use of this information. Use shall be entirely at the user's own risk.

No patent rights or licenses to any circuits described in this data sheet are implied or granted to any third party.

Peregrine's products are not designed or intended for use in devices or systems intended for surgical implant, or in other applications intended to support or sustain life, or in any application in which the failure of the Peregrine product could create a situation in which personal injury or death might occur. Peregrine assumes no liability for damages, including consequential or incidental damages, arising out of the use of its products in such applications.

The Peregrine name, logo, and UTSi are registered trademarks and UltraCMOS and HaRP are trademarks of Peregrine Semiconductor Corp.